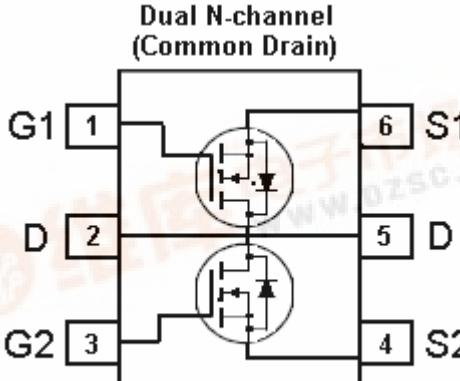
	<h2 style="text-align: center;">TSM9926D</h2> <h3 style="text-align: center;">20V Dual N-Channel Enhancement Mode MOSFET</h3>							
	<p>Pin assignment:</p> <ol style="list-style-type: none"> 1. Gate 1 2. Drain 3. Gate 2 4. Source 2 5. Drain 6. Source 1 	<p>$V_{DS} = 20V$</p> <p>$R_{DS(on)}, V_{GS} @ 4.5V, I_{DS} @ 6A = 30m\Omega$</p> <p>$R_{DS(on)}, V_{GS} @ 2.5V, I_{DS} @ 5.2A = 40m\Omega$</p>						
Features <ul style="list-style-type: none"> ◊ Advanced trench process technology ◊ High density cell design for ultra low on-resistance ◊ Excellent thermal and electrical capabilities ◊ Surface mount ◊ Fast switching 		Block Diagram 						
Ordering Information <table border="1" style="width: 100%; border-collapse: collapse;"> <thead> <tr> <th style="text-align: left;">Part No.</th><th style="text-align: left;">Packing</th><th style="text-align: left;">Package</th></tr> </thead> <tbody> <tr> <td>TSM9926DCX6</td><td>Tape & Reel</td><td>SOT-26</td></tr> </tbody> </table>		Part No.	Packing	Package	TSM9926DCX6	Tape & Reel	SOT-26	
Part No.	Packing	Package						
TSM9926DCX6	Tape & Reel	SOT-26						
Absolute Maximum Rating ($T_a = 25^\circ C$ unless otherwise noted)								
Parameter	Symbol	Limit	Unit					
Drain-Source Voltage	V_{DS}	20	V					
Gate-Source Voltage	V_{GS}	± 12	V					
Continuous Drain Current, $V_{GS} @ 4.5V$.	I_D	6	A					
Pulsed Drain Current, $V_{GS} @ 4.5V$	I_{DM}	30	A					
Maximum Power Dissipation	$T_a = 25^\circ C$	1.25	W					
	$T_a = 25^\circ C$ (Peak)	2	W					
Operating Junction Temperature	T_J	+150	$^\circ C$					
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ C$					
Thermal Performance								
Parameter	Symbol	Limit	Unit					
Junction to Ambient Thermal Resistance (PCB mounted)	$R_{\theta ja}$	100	$^\circ C/W$					

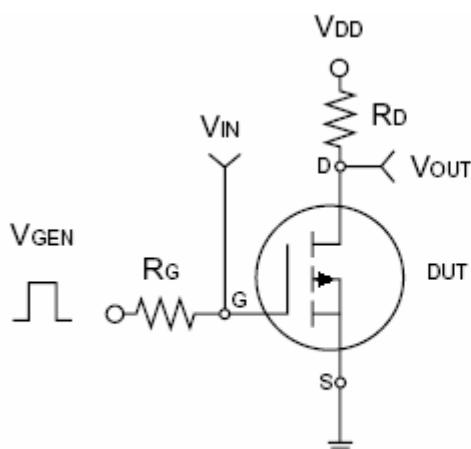
Note: Surface mounted on FR4 board $t \leq 5sec$.

Electrical Characteristics (per channel)

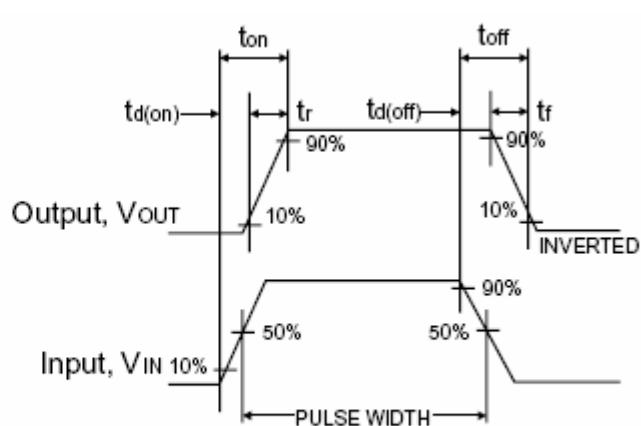
T_a = 25 °C unless otherwise noted

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Static						
Drain-Source Breakdown Voltage	V _{GS} = 0V, I _D = 250uA	BV _{DSS}	20	--	--	V
Drain-Source On-State Resistance	V _{GS} = 4.5V, I _D = 6A	R _{DS(ON)}	--	21	30	mΩ
Drain-Source On-State Resistance	V _{GS} = 2.5V, I _D = 5.2A	R _{DS(ON)}	--	30	40	mΩ
Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250uA	V _{GS(TH)}	0.6	--	--	V
Zero Gate Voltage Drain Current	V _{DS} = 20V, V _{GS} = 0V	I _{DSS}	--	--	1.0	uA
Gate Body Leakage	V _{GS} = ±12V, V _{DS} = 0V	I _{GSS}	--	--	± 100	nA
Forward Transconductance	V _{DS} = 10V, I _D = 6A	g _{fs}	7	13	--	S
Dynamic						
Total Gate Charge	V _{DS} = 10V, I _D = 6A, V _{GS} = 4.5V	Q _g	--	7.1	--	nC
Gate-Source Charge		Q _{gs}	--	1.96	--	
Gate-Drain Charge		Q _{gd}	--	2.94	--	
Turn-On Delay Time	V _{DD} = 10V, R _L = 10Ω, I _D = 1A, V _{GEN} = 4.5V, R _G = 6Ω	t _{d(on)}	--	4.9	--	nS
Turn-On Rise Time		t _r	--	2.6	--	
Turn-Off Delay Time		t _{d(off)}	--	15.7	--	
Turn-Off Fall Time		t _f	--	14	--	
Input Capacitance	V _{DS} = 10V, V _{GS} = 0V, f = 1.0MHz	C _{iss}	--	620	--	pF
Output Capacitance		C _{oss}	--	124	--	
Reverse Transfer Capacitance		C _{rss}	--	95	--	
Source-Drain Diode						
Max. Diode Forward Current		I _S	--	--	1.7	A
Diode Forward Voltage	I _S = 1.7A, V _{GS} = 0V	V _{SD}	--	--	1.2	V

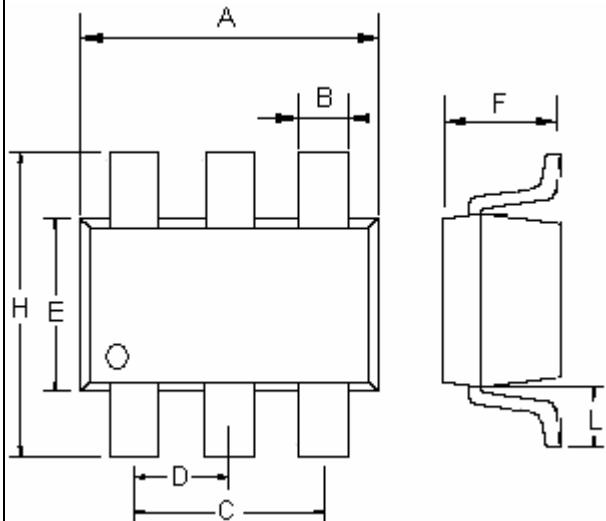
Note : pulse test: pulse width <=300uS, duty cycle <=2%



Switching Test Circuit



Switchin Waveforms

SOT-26 Mechanical Drawing

SOT-26 DIMENSION				
DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.70	3.00	0.106	0.118
B	0.25	0.50	0.010	0.020
C	1.90(typ)		0.075(typ)	
D	0.95(typ)		0.037(typ)	
E	1.50	1.70	0.059	0.067
F	1.05	1.35	0.041	0.053
H	2.60	3.00	0.102	0.118
L	0.60(typ)		0.024(typ)	